

PNP/PNP high power double bipolar transistor 22 October 2014 P

Product data sheet

### 1. General description

PNP/PNP high power double bipolar transistor in a SOT1205 (LFPAK56D) Surface-Mounted Device (SMD) power plastic package.

NPN/NPN complement: PHPT610030NK.

NPN/PNP complement: PHPT610030NPK.

### 2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

### 3. Applications

- Motor control
- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Relay replacement

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-100	V
I <sub>C</sub>	collector current			-	-	-3	А
Per transistor							
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} &I_{C} \texttt{=-2 A; I}_{B}\texttt{=-0.2 A; pulsed;} \\ &t_{p} \texttt{\leq 300 \mu s; } \delta \texttt{\leq 0.02; T}_{amb}\texttt{=25 °C} \end{split}$		-	110	180	mΩ



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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 B2 E2
2	B1	base TR1		
3	E2	emitter TR2		
4	B2	base TR2		
5	C2	collector TR2		E1 B1 C2
6	C2	collector TR2		sym138
7	C1	collector TR1	1 2 3 4 LFPAK56D (SOT1205)	
8	C1	collector TR1		

## 6. Ordering information

Table 3.     Ordering information						
Type number	Package	age				
	Name	Description	Version			
PHPT610030PK	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT610030PK	10030PK

## 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
Per transistor							
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-100	V	
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-100	V	
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V	
I <sub>C</sub>	collector current			-	-3	А	
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-8	А	
IB	base current			-	-0.5	А	
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Symbol	Parameter	Conditions		Min	Мах	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1	W
			[2]	-	2.4	W
			[3]	-	25	W
Per device		,				,
P <sub>tot</sub> to	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[4]	-	5	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

- [3] Power dissipation from junction to mounting base.
- [4] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

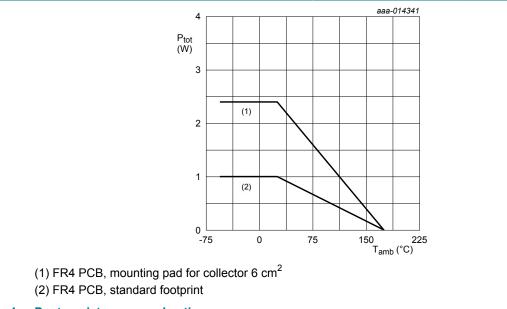


Fig. 1. Per transistor: power derating curves

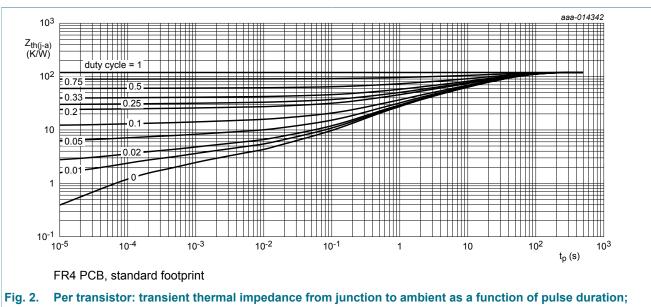
#### PNP/PNP high power double bipolar transistor

### 9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	150	K/W
	from junction to ambient	-	[2]	-	-	62.5	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	6	K/W
Per device		·					
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	120	K/W
from junction to ambient			[2]	-	-	50	K/W
	ambient		[3]	-	-	30	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

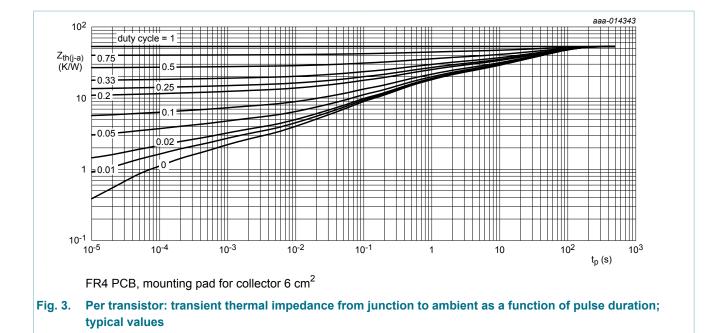


typical values

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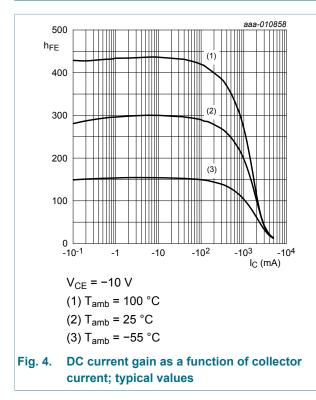
### **10. Characteristics**

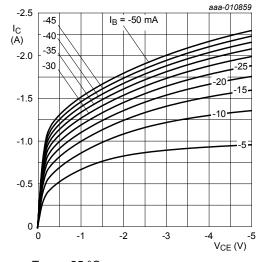
#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transist	tor	·				
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -80 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -7 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub> DC current gain	DC current gain	$V_{CE}$ = -10 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	150	220	-	
		$\begin{split} V_{CE} &= -10 \text{ V; } I_C = -1 \text{ A; pulsed;} \\ t_p &\leq 300  \mu\text{s; } \delta \leq 0.02\text{; } T_{amb} = 25 ^\circ\text{C} \end{split}$	80	210	-	
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -2 \text{ A}; \text{ pulsed};$ $t_{p} \leq 300  \mu\text{s};  \delta \leq 0.02;  T_{amb} = 25 ^{\circ}\text{C}$	20	100	-	
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -3 \text{ A}; \text{ pulsed};$ $t_{p} \leq 300  \mu\text{s};  \delta \leq 0.02;  T_{amb} = 25 ^{\circ}\text{C}$	10	40	-	
OLSAI	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-70	-110	mV
		$\begin{split} I_{C} &= -2 \text{ A};  I_{B} = -200 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \delta \leq 0.02;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-220	-360	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} I_{C} &= -2 \text{ A};  I_{B} = -0.2 \text{ A}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \delta \leq 0.02;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	110	180	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.91	-1	V
		$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-1.02	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$\label{eq:VcE} \begin{array}{l} V_{CE} = -2 \ V; \ I_{C} = -100 \ mA; \ pulsed; \\ t_{p} \leq 300 \ \mus; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	-	-0.68	-0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = -12.5 V; I <sub>C</sub> = -1 A; I <sub>Bon</sub> = -50 mA;	-	20	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	180	-	ns
t <sub>on</sub>	turn-on time		-	200	-	ns
t <sub>s</sub>	storage time		-	350	-	ns
t <sub>f</sub>	fall time		-	220	-	ns
t <sub>off</sub>	turn-off time		-	570	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	125	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	30	-	pF





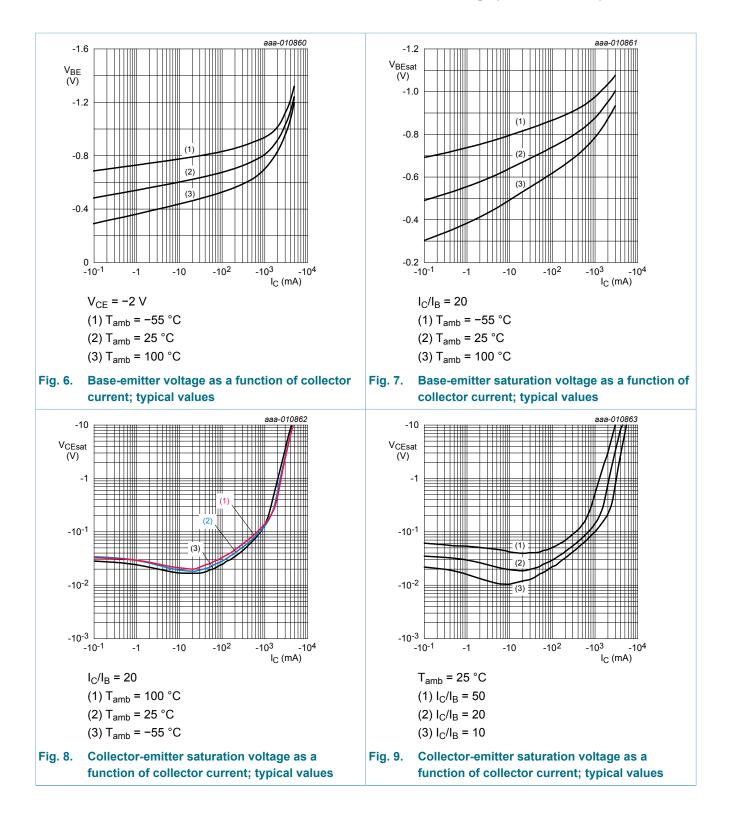
T<sub>amb</sub> = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values

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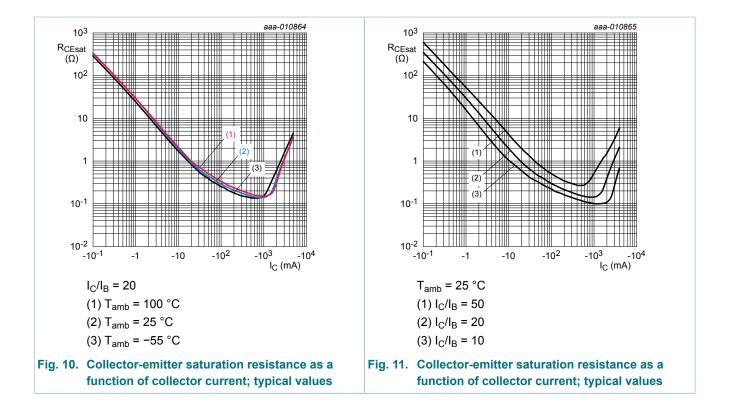
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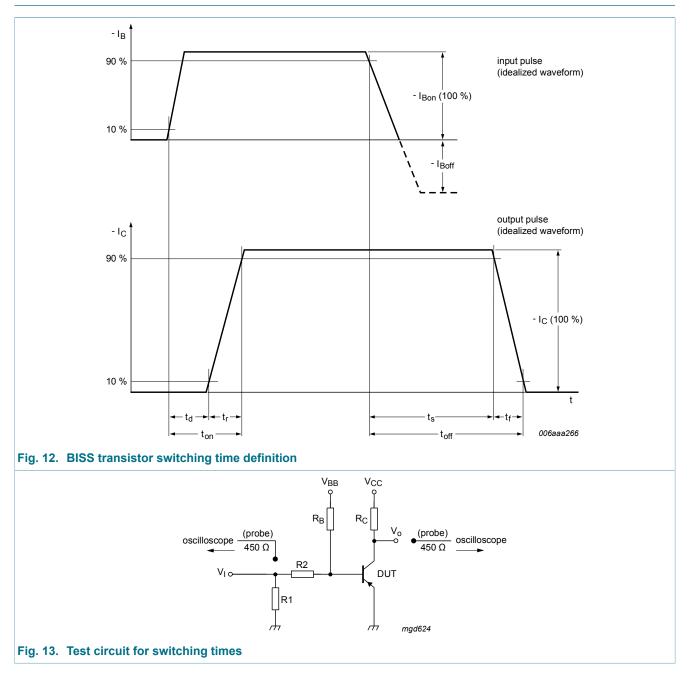
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### **11. Test information**

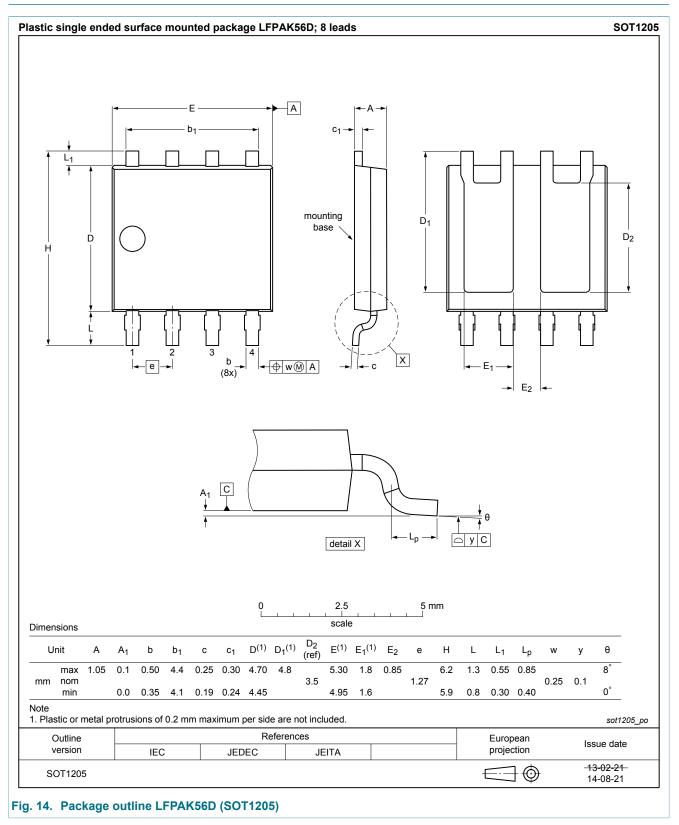
### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 12. Package outline



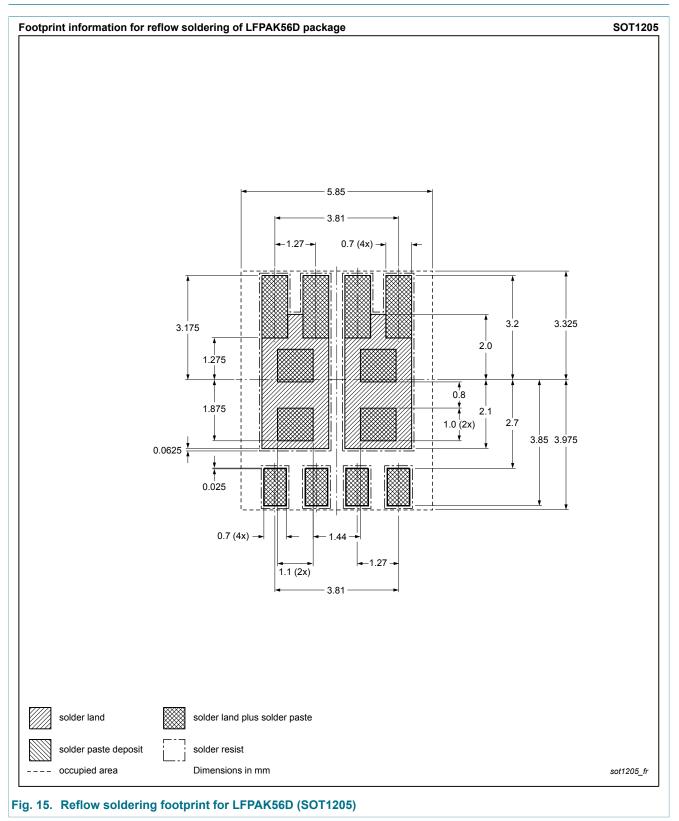
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### 13. Soldering



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## 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PHPT610030PK v.1	20141022	Product data sheet	-	-		

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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